SAMYANG ELECTRONICS

1N5400 --- 1N5408

PLASTIC SILICON RECTIFIER

VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 3.0 A

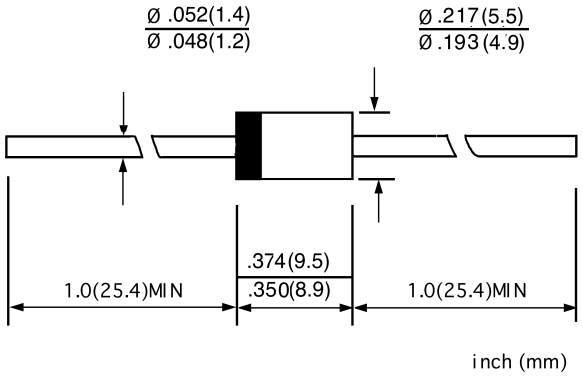
FEATURES

- ◇ Low cost
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO--27,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.041 ounces,1.15 grams
- ◇ Mounting position: Any

DO - 27



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		1N 5400	1N 5401	1N 5402	1N 5403	1N 5404	1N 5405	1N 5406	1N 5407	1N 5408	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	300	400	500	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	210	280	350	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	300	400	500	600	800	1000	V
Maximum average forw ard rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	3.0									A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_J=125℃	I_{FSM}	200.0									A
Maximum instantaneous forw ard voltage @ 3.0 A	V_F	1.0									V
Maximum reverse current @T_A=25℃ at rated DC blocking voltage @T_A=100℃	I_R	10.0 100.0									μA
Typical junction capacitance (Note1)	C_J	35									pF
Typical thermal resistance (Note2)	R_{JA}	20									℃
Operating junction temperature range	T_J	- 55 ---- + 150									℃
Storage temperature range	T_{STG}	- 55 ---- + 150									℃

NOTE: 1. Measured at 1.0MHz and applied rev erse v oltage of 4.0V DC.
2. Thermal resistance from junction to ambient.

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FIG.1 – FORWARD DERATING CURVE

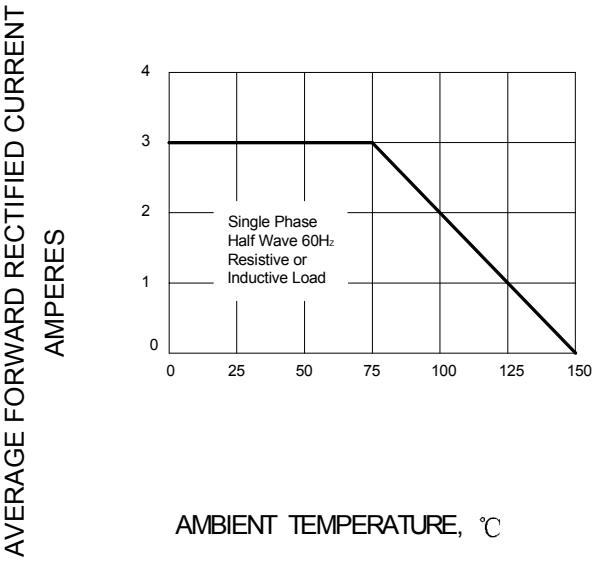


FIG.2 – PEAK FORWARD SURGE CURRENT

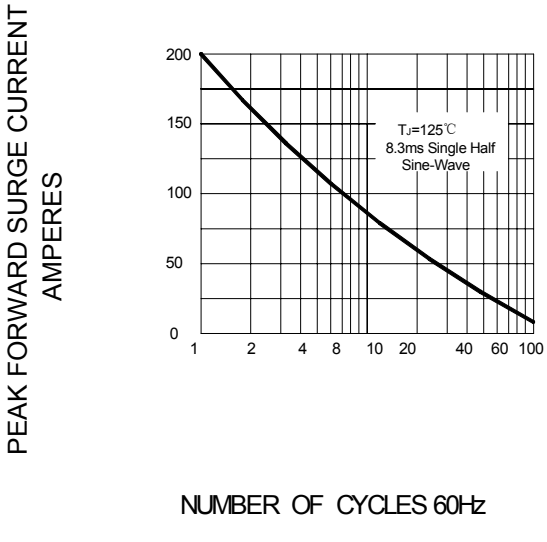


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

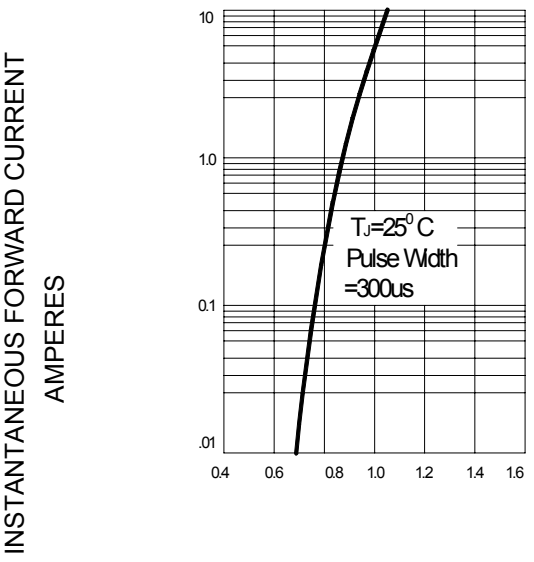


FIG.4 – TYPICAL JUNCTION CAPACITANCE

